

PATENT APPLICATION  
S/N 08/327,887

On page 6, lines 11-15, kindly delete the paragraph "Fig. 2D is a cross-sectional view...the selective tungsten thin films 10.", and insert therefor ~~Fig. 2D is a cross-sectional view~~ illustrating that the second contact hole 40 above the first contact hole 30, as fabricated in Fig. 2C, is almost filled by the CVD method with selective tungsten thin films 10 in contact with the selective tungsten thin films 9 of the first contact hole 30, and that the second contact hole 40 above the polysilicon 7 is simultaneously almost filled with selective tungsten thin films 10 by the CVD method.--

IN THE CLAIMS

Kindly amend Claims 1, 3, and 4 as follows:

1. (AMENDED) A method for filling contact holes with metal by two-step deposition of selective tungsten layers, said method comprising the steps of:
  - providing a silicon substrate;
  - forming a field oxide layer and a junction layer and gate electrode on said silicon substrate;
  - forming a first insulating layer on the whole structure;
  - forming first contact holes by removing [the] (desired) portions of the first insulating layer to expose said junction layer and said gate electrode, respectively;
  - filling first metal layers into the first contact holes, entirely;
  - forming a conductive layer pattern on the first insulating layer spaced from said first metal layers;
  - forming a second insulating layer on the whole structure;
  - forming a plurality of second contact holes of substantially equal depth by removing [the] (desired) portions of said second insulating layer to expose both the first metal layers and the conductive layer pattern, respectively; and
  - filling [a] second metal layers into said plurality of second contact holes to contact with the first metal layers and the conductive layer pattern, respectively.

3. (AMENDED) A method for filling contact holes with metal by two-step deposition